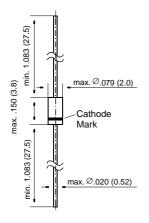
SD101A THRU SD101C

Schottky Diodes

<u>DO-35</u>



Dimensions in inches and (millimeters)

FEATURES

- For general purpose applications.
- The LL101 series is a metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing, and coupling diodes for fast switching and low logic level applications.
- These diodes are also available in the SOD-123 case with type designations SD101AW thru SD101CW and in the MiniMELF case with type designations LL101A thru LL101C.

MECHANICAL DATA

Case: DO-35 Glass Case **Weight:** approx. 0.13 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

60 50 40	V V
	V
400 ^{1) 2)}	mW
2	A
1251)	°C
-55 to +150 ¹⁾	°C
	$-55 \text{ to } +150^{1)}$



SD101A THRU SD101C

ELECTRICAL CHARACTERISTICS

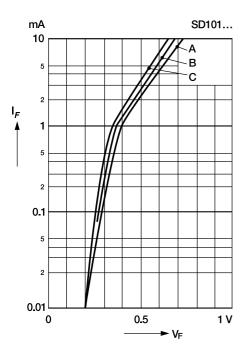
Ratings at 25 °C ambient temperature unless otherwise specified

		Symbol	Min.	Тур.	Max.	Unit	
Reverse Breakdown Voltage at I _R = 10 μA	SD101A SD101B SD101C	V(br)r V(br)r V(br)r	60 50 40			V V V	
Leakage Current at $V_R = 50 V$ at $V_R = 40 V$ at $V_R = 30 V$	SD101A SD101B SD101C	I _R I _R I _R	- - -		200 200 200	nA nA nA	
Forward Voltage Drop at I _F = 1 mA at I _F = 15 mA	SD101A SD101B SD101C SD101A SD101B SD101C	VF VF VF VF VF VF	- - - - -	- - - - -	0.41 0.4 0.39 1 0.95 0.9	V V V V V	
Junction Capacitance at $V_R = 0 V$, f = 1 MHz	SD101A SD101B SD101C	C _{tot} C _{tot} C _{tot}	- - -		2.0 2.1 2.2	pF pF pF	
Reverse Recovery Time at $I_F = I_R = 5$ mA, recover to 0.1 I_R		t _{rr}	_	-	1	ns	
Thermal Resistance, Junction to Ambient Air		R _{thJA}	_	-	0.31)	K/mW	
¹⁾ Valid provided that leads at a distance of 4 mm from case are kept ambient temperature							

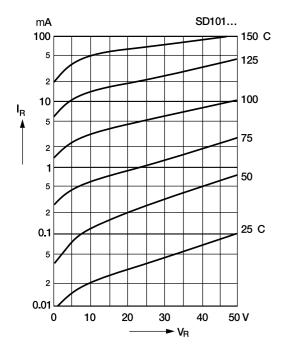


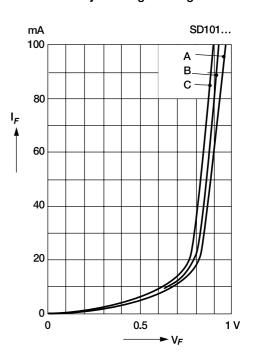
RATINGS AND CHARACTERISTIC CURVES SD101A THRU SD101C

Typical variation of fwd. current vs. fwd. voltage for primary conduction through the Schottky barrier

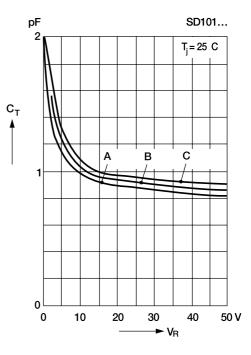


Typical variation of reverse current at various temperatures





Typical capacitance curve as a function of reverse voltage





Typical forward conduction curve of combination Schottky barrier and PN junction guard ring